

L Number	Hits	Search Text	DB	Time stamp
1	820	aluminate and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/21 15:52
4	129	(aluminate and semiconductor) and lanthanum	USPAT	2002/08/21 16:22
5	120	((aluminate and semiconductor) and lanthanum) and (nitrogen aluminum silicon oxygen)	USPAT	2002/08/21 16:22
6	109	(((aluminate and semiconductor) and lanthanum) and (nitrogen aluminum silicon oxygen)) and (dielectric electrode conduct\$3)	USPAT	2002/08/21 16:22
7	96	(((aluminate and semiconductor) and lanthanum) and (nitrogen aluminum silicon oxygen)) and (dielectric electrode conduct\$3)) and substrate	USPAT	2002/08/21 16:23
9	5	((((aluminate and semiconductor) and lanthanum) and (nitrogen aluminum silicon oxygen)) and (dielectric electrode conduct\$3)) and substrate) and lanthanum near3 aluminum	USPAT	2002/08/21 16:23
10	179	(aluminate and semiconductor) and lanthanum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/21 16:22
11	162	((aluminate and semiconductor) and lanthanum) and (nitrogen aluminum silicon oxygen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/21 16:22
12	148	(((aluminate and semiconductor) and lanthanum) and (nitrogen aluminum silicon oxygen)) and (dielectric electrode conduct\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/21 16:23
13	96	((((aluminate and semiconductor) and lanthanum) and (nitrogen aluminum silicon oxygen)) and (dielectric electrode conduct\$3)) and substrate	USPAT	2002/08/21 16:23
14	5	((((aluminate and semiconductor) and lanthanum) and (nitrogen aluminum silicon oxygen)) and (dielectric electrode conduct\$3)) and substrate) and lanthanum near3 aluminum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/21 16:39
15	38	semiconductor and lanthanum adj aluminum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/21 16:40



- ✓ L1: (16) (aluminate and semiconductor) and (lanthanum with (nitrogen nitride
- ✓ L2: (205) (lanthanum same (nitrogen nitride\$4)) and aluminate
- ✓ L3: (5) 'La' \$3 'Al' \$3 'O' \$3 'N'
- ✓ L4: (21) La adj3 Al adj3 O\$3
- ✓ L5: (5) 'La' adj3 'Al' adj3 'O' adj3 'N'\$3
- ✓ L6: (0) (lanthanum adj aluminate) and (oxygen nitrogen aluminum)
- ✓ L7: (227) (lanthanum adj aluminate) and (oxygen nitrogen aluminum)
- ✓ L8: (132) 7 and (dielectric insulat\$3)
- ✓ L9: (125) 8 and substrate
- ✓ L10: (48) 9 and semiconductor
- ✓ L11: (4) 'La' adj2 'Al' adj2 'O' adj2 'N'
- ✓ L12: (600) La\$3Al\$3O\$3N\$3
- ✓ L14: (86) La\$2Al\$2O\$2N\$3
- ✓ L13: (47) La\$2Al\$2O\$2N\$2
- ✓ **L15: (5) La adj3 Al adj3 O adj3 N\$3**
- ✓ L16: (1) "5141802".PN.

Search

DBs: ☒ Plurals

Default operator: ☒ Highlight all hit terms initially

La adj3 Al adj3 O adj3 N\$3

BRS form IS&R form Image Text HTML

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 5403792 A	19950404	5	Low thermal conductivity ceramic and process for producing the same	501/98.2	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 5262469 A	19931116	6	Oxynitride glass fiber for composite products and glass fiber-reinforced p	524/494	428/373;
3	<input type="checkbox"/>	<input type="checkbox"/>	US 4957883 A	19900918	16	Oxynitride glass and the fiber thereof	501/35	428/391;
4	<input type="checkbox"/>	<input type="checkbox"/>	EP 564257 A	19931006	5	Low thermal conductivity sialon ceramic - obtd. by mixing sialon with		501/56;
5	<input type="checkbox"/>	<input type="checkbox"/>	JP 63176340 A	19880720	3	Glass fibre used for reinforcing composite material - is obtd. by fusin		501/73;

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- ✎ L5: (17) La adj3 N adj3 O\$3
- ✎ L7: (0) La adj3 N adj3 aluminate
- ✎ L6: (97) 'La' near3 'N' near3 'O'
- ✎ L9: (3432161) La near3 N nera3 Al
- ✎ L8: (33) La adj3 N adj3 al
- ✎ L10: (9) Al adj3 La adj3 N
- ✎ L11: (62) 'Al' near3 'La' near3 'N'

- ✎ L13: (10) "197394"
- ✎ L14: (0) 6 and "197394"
- ✎ L15: (0) 2020/0197394
- ✎ L12: (82) La near3 N near3 Al
- ✎ L17: (48) 'N' near2 'Al' near2 'La'
- ✎ L16: (17) 'Al' near2 'La' near2 'N'

 **Saved**

☛ (820) aluminate and semiconductor

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'Al' near2 'La' near2 'N'

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20020172613 A1	20021121	15	Fe-cr-al based alloy foil and method for producing the same	420/34	420/8; 428/606
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6475483 B1	20021105	63	Method for in vitro proliferation of dendritic cell precursors and their use	424/93.7	435/372
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6177351 B1	20010123	28	Method and structure for etching a thin film perovskite layer	438/694	438/710; 438/712;
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6171970 B1	20010109	16	Method for forming high-density integrated circuit capacitors	438/706	438/710; 438/712;
5			US 6152400 A	20001128	20	Method for forming integrated circuit	428/206	428/240;